

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	tzeng near kai.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	26	wu near cheng-ming.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	16	hu near chu-wei.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	39893	hsu nar kuei-yuam.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
5	BRS	L5	0	("2005/0087864").URPN.	USPAT

	Type	L #	Hits	Search Text	DBs
6	BRS	L6	7	(bonding near pad) near25 (glass near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	228	(pad) near25 (glass near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	45	(pad) near25 (glass near3 temperature) near25 (polym\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
9	BRS	L9	873	(bond\$3) near25 (glass near3 temperature) near25 (polym\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
10	BRS	L10	27	((bond\$3) near25 (glass near3 temperature) near25 (polym\$5)) near15 (thermal)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	7	((bond\$3) near25 ("t.sub.g") near25 (polym\$5)) near15 (thermal)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	0	((pad) near25 ("t.sub.g") near25 (polym\$5)) near15 (thermal)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
13	BRS	L13	4	((pad) near25 ("t.sub.g") near25 (polym\$5)) and (thermal)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
14	BRS	L14	5	((pad) near25 ("t.sub.g") near25 (polym\$5))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	4999	((("t.sub.g") near25 (polym\$5))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	765	((below) near10 ("t.sub.g") near25 (polym\$5))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
17	BRS	L17	165941	"438"/\$.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
18	BRS	L18	17	16 and 17	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	976	((above) near10 ("t.sub.g") near25 (polym\$5))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	13	17 and 19	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
21	BRS	L21	386	16 and 19	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
22	BRS	L22	239	21 and (pad or bond\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	239	21 and (pad or bond\$3 or bump)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	225	23 and (glass near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
25	BRS	L25	32	23 and ((glass near3 temperature) near15 (thermal))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
26	BRS	L26	32332	((glass near3 temperature) or ("t.sub.g")) near25 (polym\$5))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	32332	((glass near3 temperature) or ("t.sub.g")) near25 (polym\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	48	((glass near3 temperature) or ("t.sub.g")) near25 (polym\$5)) near25 (pad)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
29	BRS	L29	954	((glass near3 temperature) or ("t.sub.g")) near25 (polym\$5)) near25 (bond\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
30	BRS	L30	128	((glass near3 temperature) or ("t.sub.g")) near25 (polyi\$5)) near25 (bond\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L31	2	((glass near3 temperature) or ("t.sub.g")) near25 (polyi\$5)) near25 (pad)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
32	BRS	L32	3	((glass near3 temperature) or ("t.sub.g")) near25 (polyi\$5)) near25 (bump)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
33	BRS	L33	128	((glass near3 temperature) or ("t.sub.g")) near25 (polyi\$5)) near25 (bond\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
34	BRS	L34	27	33 and (semiconductor near device)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
35	BRS	L35	8	((((below) near15 (glass near3 temperature) or ("t.sub.g")) near25 (polyi\$5)) near25 (bond\$3 or pad or bump))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
36	BRS	L36	1	((((below) near15 (glass near3 temperature) or ("t.sub.g")) near25 (passivation)) near25 (bond\$3 or pad or bump))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
37	BRS	L37	2	((glass near3 temperature) or ("t.sub.g")) near25 (passivation)) near25 (bond\$3 or pad or bump)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
38	BRS	L38	7925	(thermal) near15 (glass near3 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
39	BRS	L39	156	((thermal) near15 (glass near3 temperature)) near15 (paasivation or polyim\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
40	BRS	L40	87	39 and (pad or bump or bond\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20050022865 A1	Photovoltaic devices comprising layer(s) of photoactive organics dissolved in high Tg polymers
2			US 20040063250 A1	Process and an apparatus for the formation of patterns in films using temperature gradients
3			US 20040038513 A1	Fabrication of semiconductor devices with air gaps for ultra low capacitance interconnections and methods of making same
4			US 20040012076 A1	Porous low-dielectric constant materials for use in electronic devices
5			US 20020132496 A1	Ultra low-k dielectric materials
6			US 20020090761 A1	Package with low stress hermetic seal
7			US 20020081787 A1	Fabrication of semiconductor devices with air gaps for ultra low capacitance interconnections and methods of making same
8			US 6670285 B2	Nitrogen-containing polymers as porogens in the preparation of highly porous, low dielectric constant materials

	U	1	Document ID	Title
9			US 6610593 B2	Fabrication of semiconductor device with air gaps for ultra low capacitance interconnections and methods of making same
10			US 6459160 B1	Package with low stress hermetic seal
11			US 6342454 B1	Electronic devices with dielectric compositions and method for their manufacture
12			US 6342407 B1	Low stress hermetic seal
13			US 6165890 A	Fabrication of a semiconductor device with air gaps for ultra-low capacitance interconnections

	U	1	Document ID	Title
14			US 5783465 A	Compliant bump technology
15			US 5171716 A	Method of manufacturing semiconductor device with reduced packaging stress
16			US 4481049 A	Bilevel resist
17			US 4081277 A	Method for making a solid-state color imaging device having an integral color filter and the device